



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

2SA1417/2SC3647 — High-Voltage Switching Applications

PNP / NPN Epitaxial Planar Silicon Transistor

Features

- Adoption of FBET, MBIT processes
- High breakdown voltage and large current capacity
- Fast switching speed
- Ultrasmall size making it easy to provide high-density small-sized hybrid ICs

Specifications () : 2SA1417

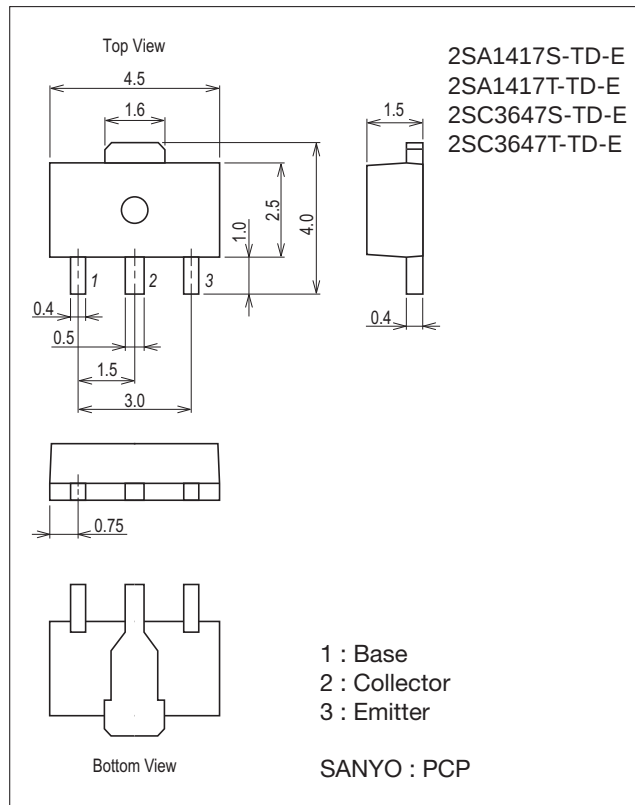
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		(-)120	V
Collector-to-Emitter Voltage	V _{CEO}		(-)100	V
Emitter-to-Base Voltage	V _{EB0}		(-)6	V
Collector Current	I _C		(-)2	A
Collector Current (Pulse)	I _{CP}		(-)3	A
Collector Dissipation	P _C		500	mW
		When mounted on ceramic substrate (250mm ² ×0.8mm)	1.5	W
Junction Temperature	T _j		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Package Dimensions

unit : mm (typ)

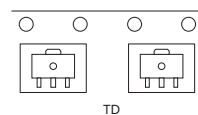
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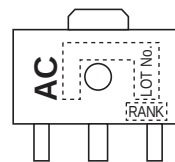
Product & Package Information

- Package : PCP
- JEITA, JEDEC : SC-62, SOT-89, TO-243
- Minimum Packing Quantity : 1,000 pcs./reel

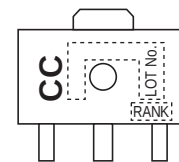
Packing Type: TD



Marking

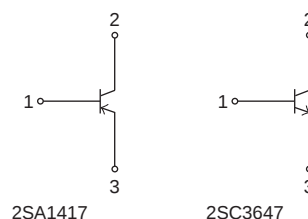


2SA1417



2SC3647

Electrical Connection



SANYO Semiconductor Co., Ltd.

<http://www.sanyosemi.com/en/network/>

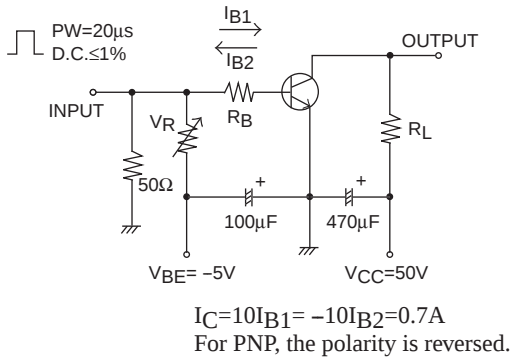
Electrical Characteristics at $T_a=25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)100\text{V}$, $I_E=0\text{A}$			$(-)100$	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)4\text{V}$, $I_C=0\text{A}$			$(-)100$	nA
DC Current Gain	h_{FE}	$V_{CE}=(-)5\text{V}$, $I_C=(-)100\text{mA}$	100*		400*	
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10\text{V}$, $I_C=(-)100\text{mA}$		120		MHz
Output Capacitance	C_{ob}	$V_{CB}=(-)10\text{V}$, $f=1\text{MHz}$		(25)16		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)1\text{A}$, $I_B=(-)100\text{mA}$		$(-0.22)0.13$	$(-0.6)0.4$	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)1\text{A}$, $I_B=(-)100\text{mA}$		$(-)0.85$	$(-)1.2$	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu\text{A}$, $I_E=0\text{A}$	$(-)120$			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1\text{mA}$, $R_{BE}=\infty$	$(-)100$			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu\text{A}$, $I_C=0\text{A}$	$(-)6$			V
Turn-On Time	t_{on}	See specified Test Circuit.		(80)80		ns
Storage Time	t_{stg}			(750)1000		ns
Fall Time	t_f			(40)50		ns

* : The 2SA1417 / 2SC3647 are classified by 100mA h_{FE} as follows :

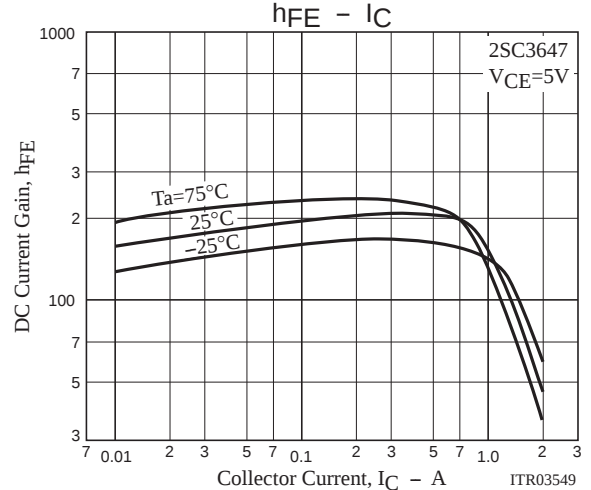
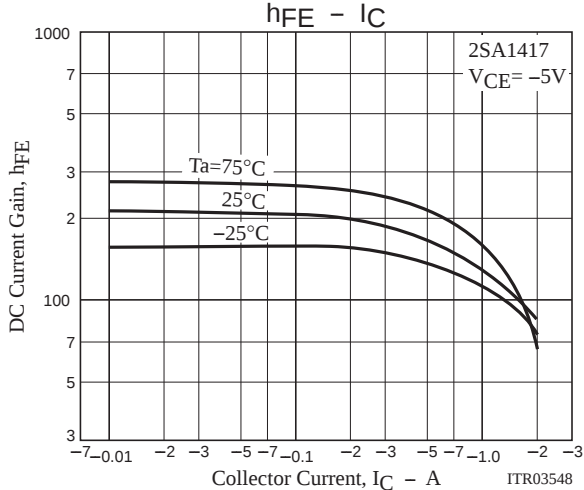
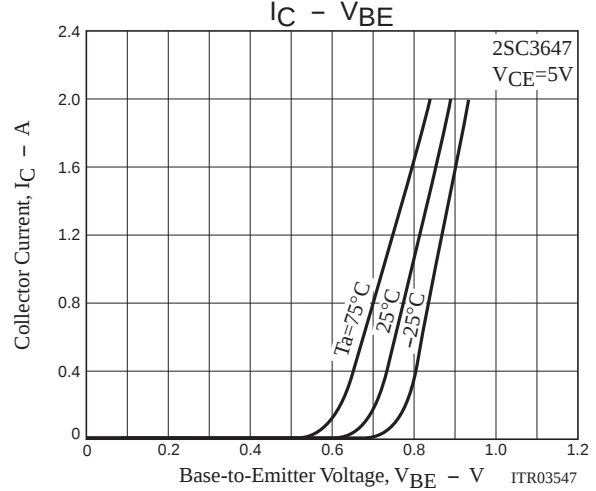
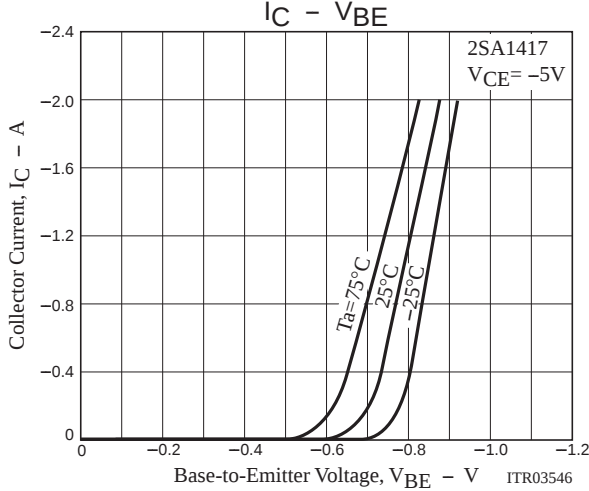
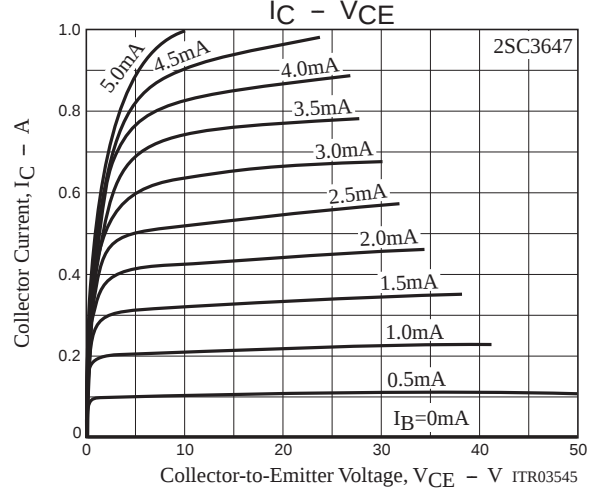
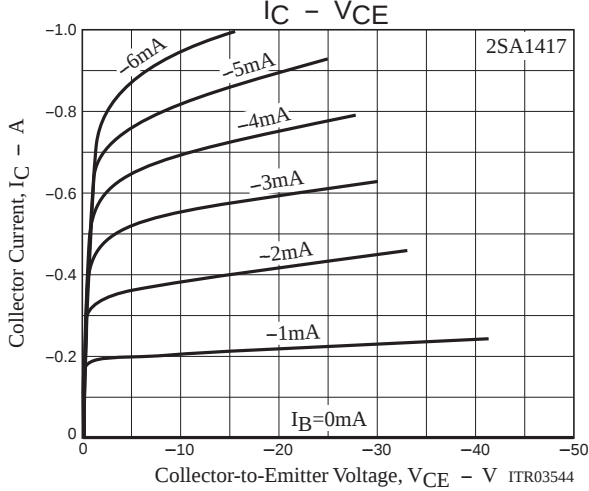
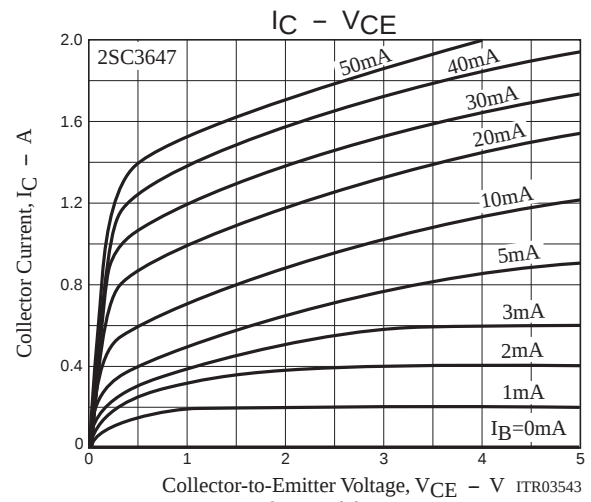
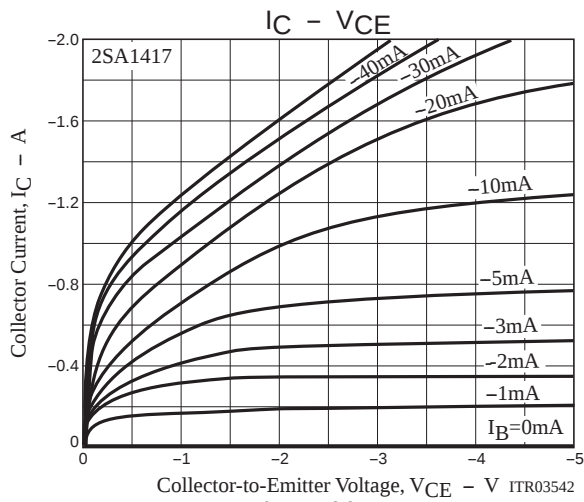
Rank	R	S	T
h_{FE}	100 to 200	140 to 280	200 to 400

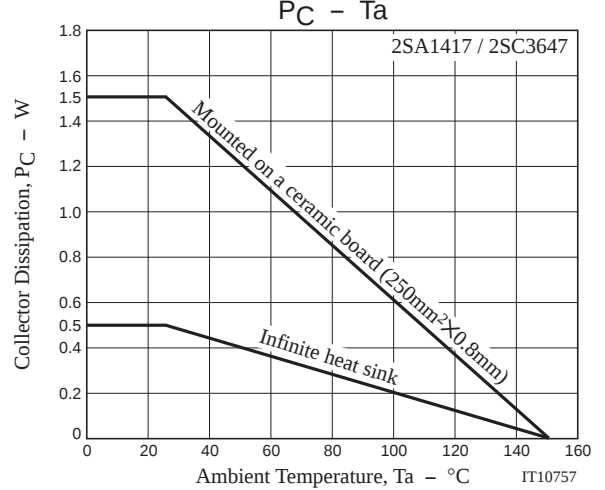
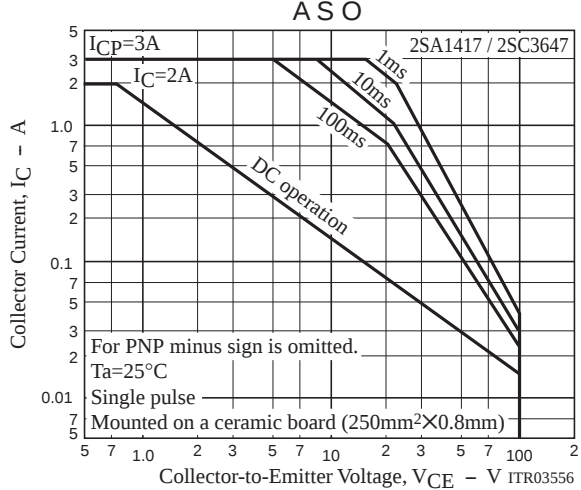
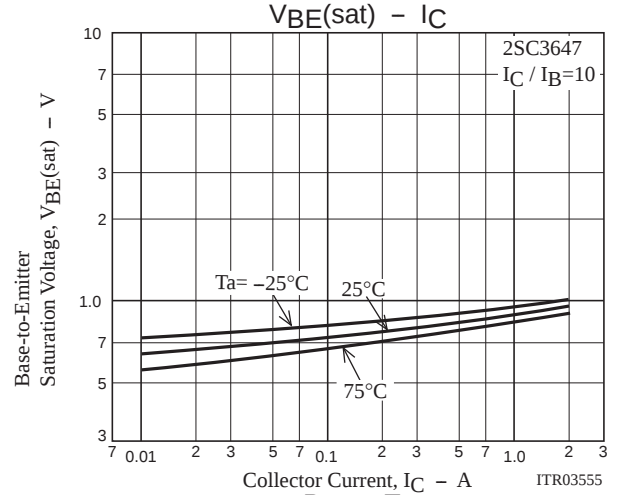
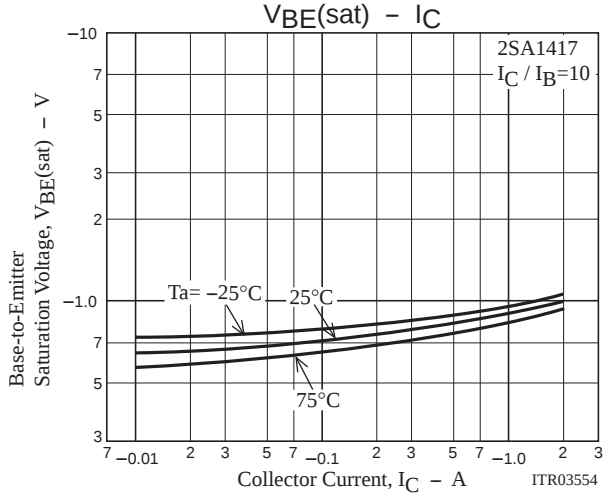
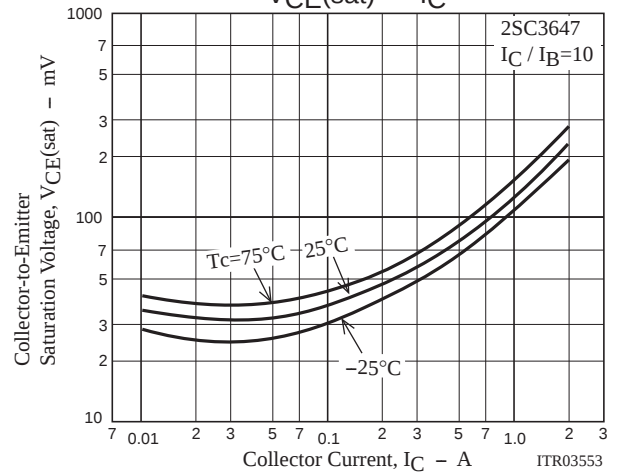
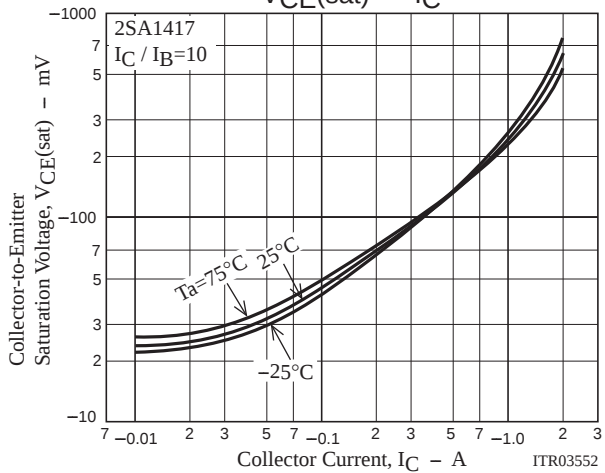
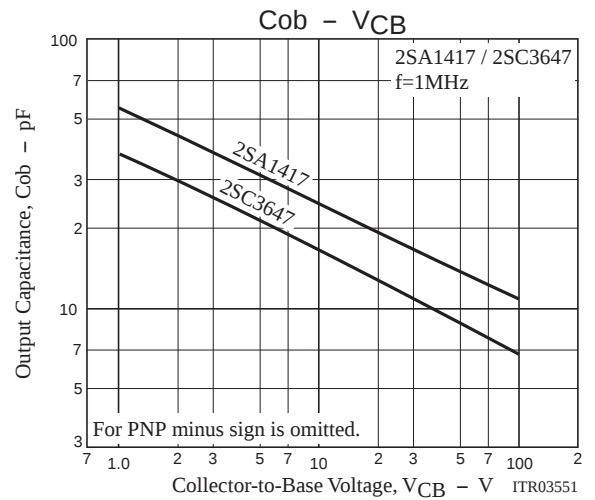
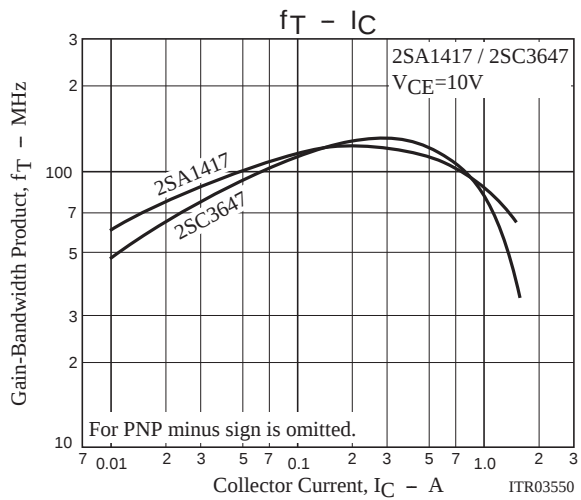
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
2SA1417S-TD-E	PCP	1,000pcs./reel	Pb Free
2SA1417T-TD-E	PCP	1,000pcs./reel	
2SC3647S-TD-E	PCP	1,000pcs./reel	
2SC3647T-TD-E	PCP	1,000pcs./reel	





Embossed Taping Specification

2SA1417S-TD-E, 2SA1417T-TD-E, 2SC3647S-TD-E, 2SC3647T-TD-E

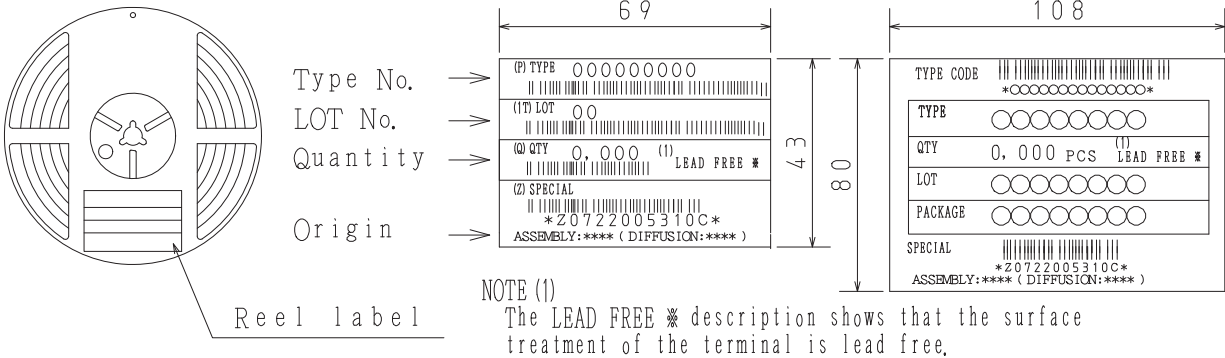
1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
PCP	PCP	1,000	4,000	24,000	4 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Reel label, Inner box label
(unit:mm)

Outer box label
It is a label at the time of factory shipments.
The form of a label may change in physical distribution process.

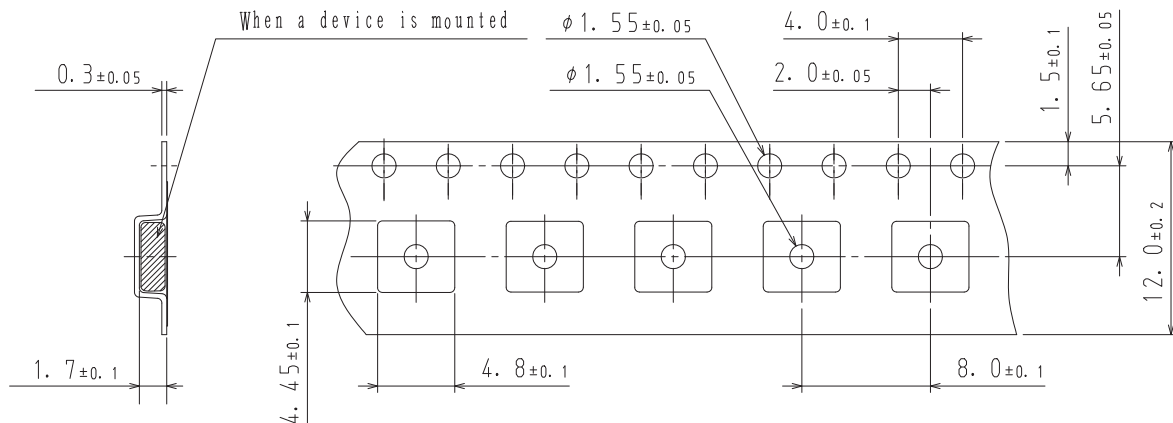
Packing method



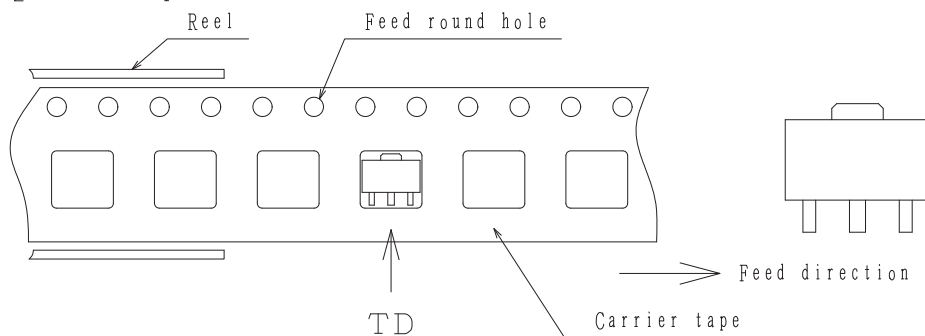
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction

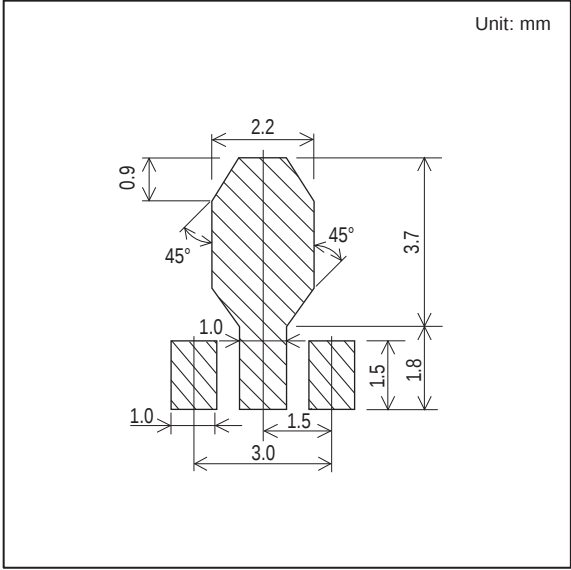
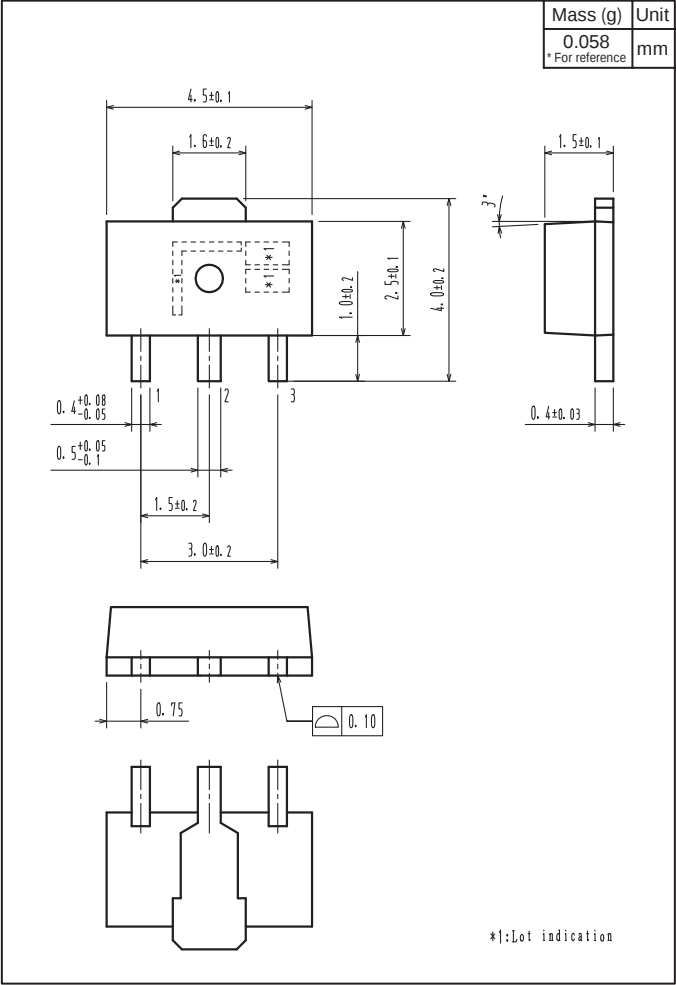


Those with pin 1 index on the feed hole side.....TD

Outline Drawing

Land Pattern Example

2SA1417S-TD-E, 2SA1417T-TD-E, 2SC3647S-TD-E, 2SC3647T-TD-E



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